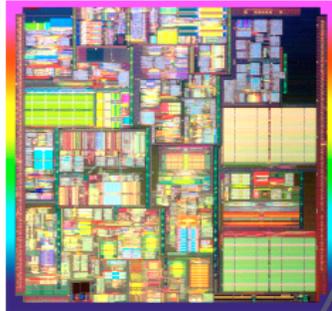
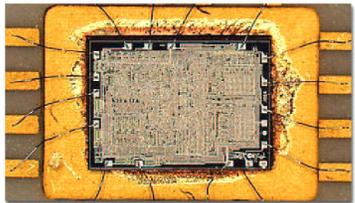
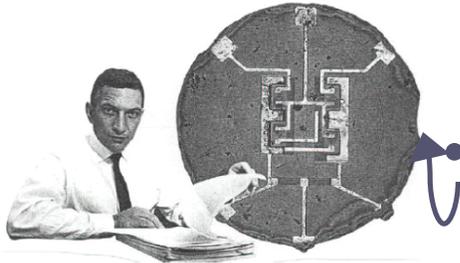
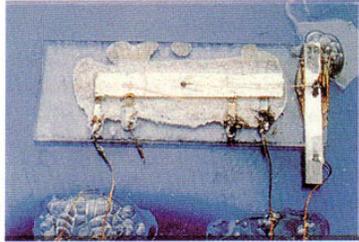
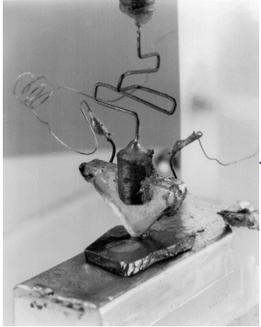
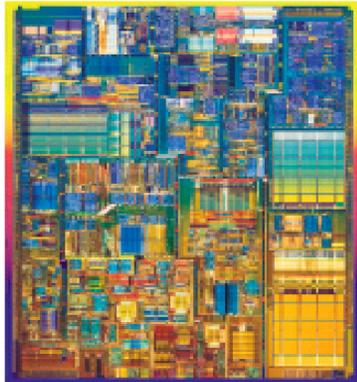


Evoluzione dei circuiti integrati



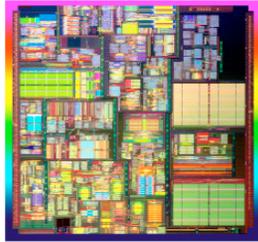
- 23 dicembre 1947, Shockley, Brattain e Bardeen (premio Nobel per la Fisica 1956) primo transistor
- 1958 Kilby (premio Nobel 2000 per la fisica) primo circuito integrato
- -1959 Noyce: primo circuito integrato monolitico
- 1970 Intel 4004
 - 2300 transistori p-MOS $8\mu\text{m}$
- 2000 Intel Pentium 4
 - $\sim 50\text{mln}$ transistori CMOS $0.13\mu\text{m}$

Evoluzione dei circuiti integrati

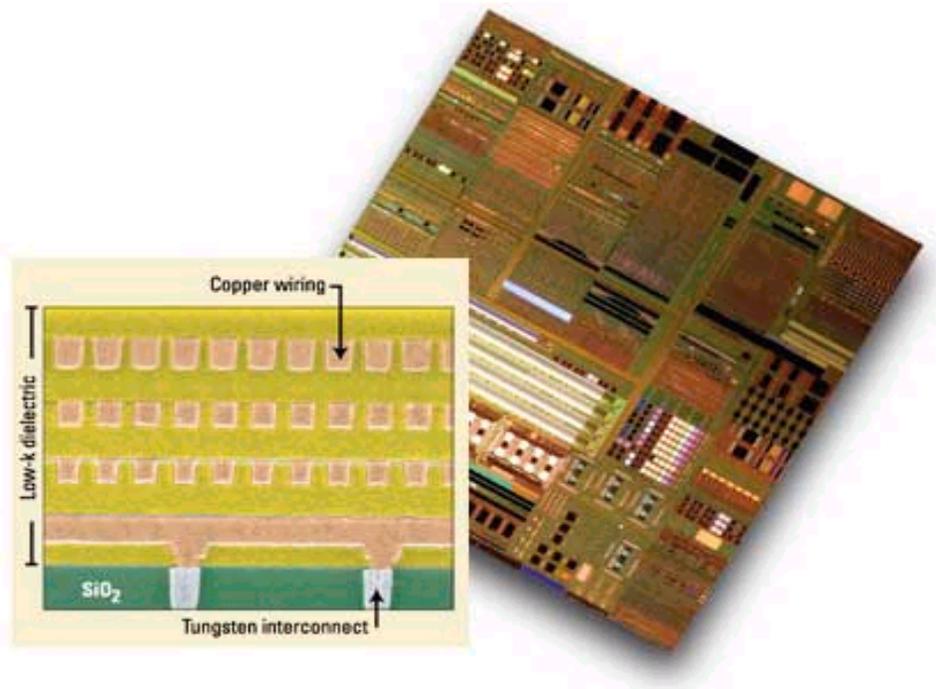


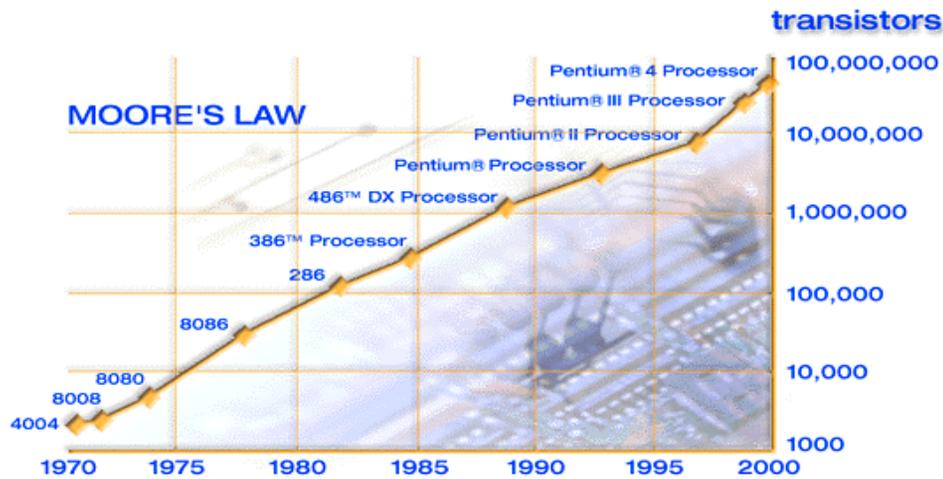
180 nm Technology

130 nm
Technology



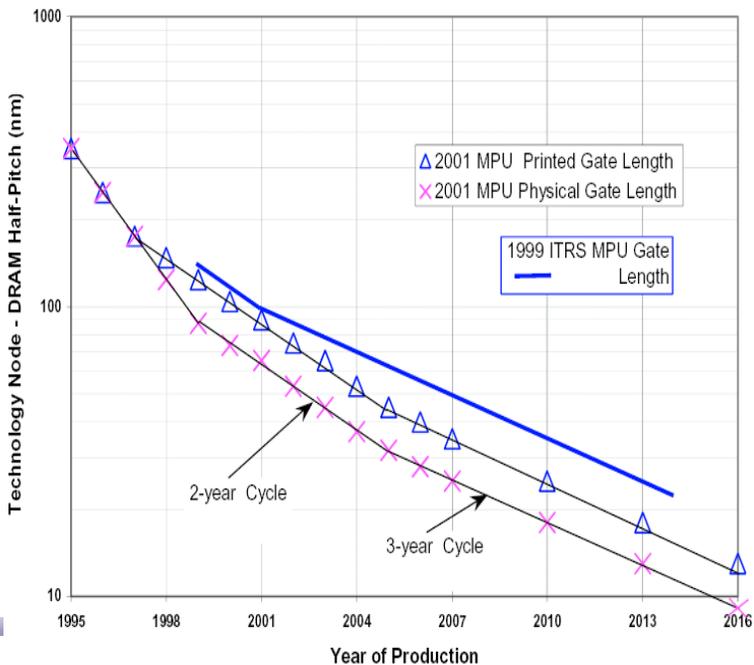
- *1998* Struttura rame dual-damascene
- *2000* Dielettrici low-k
- ASIC IBM Cu-11
 - 0.13 μm Rame e SILk
 - 30% prestazioni \uparrow
 - 50% potenza dissipata \downarrow



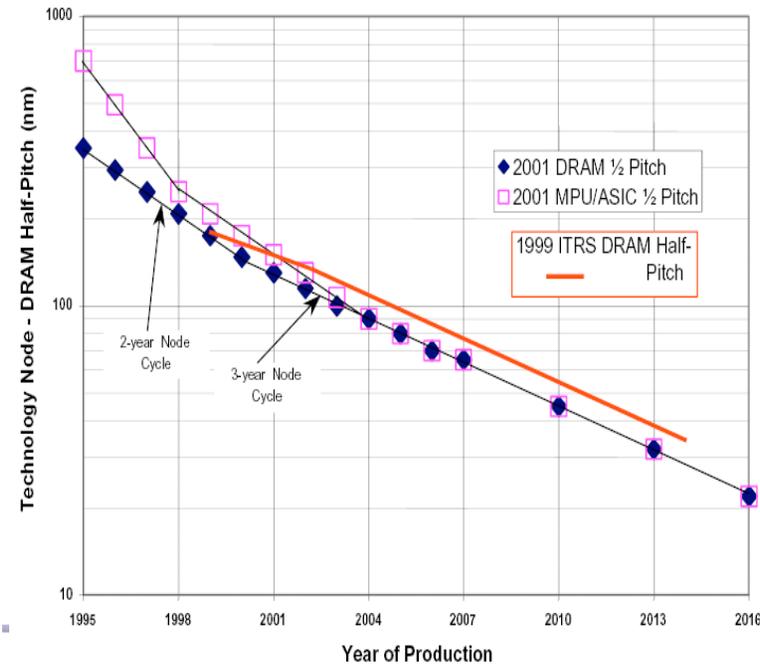


- Legge di Moore
 - N° trans/IC 2x ogni 18 mesi
 - Dim. minima 0.7x ogni 3 anni
 - Area IC 1.5x ogni 3 anni
 - Freq. Clock 1.5x ogni 3 anni
 - Costo/trans 0.5x ogni 3 anni
 - Costo Fab 2.3x ogni 3 anni
- ITRS Roadmap

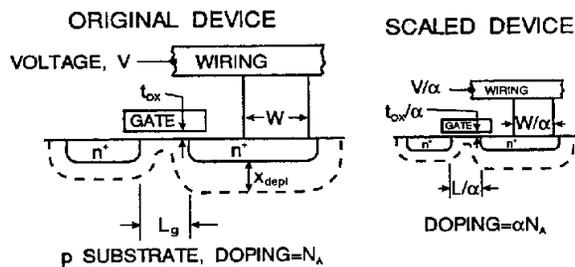
ITRS Roadmap Acceleration Continues...Gate Length



ITRS Roadmap Acceleration Continues...Half Pitch



Si ringrazia l'Ing. Junior Paolo RIVA per le trasparenze



- Miglioramento prestazioni:

- Scaling

- Ritardo RC:

- Ritardo di gate ↓
- Ritardo delle interconnessioni ↑

- Soluzioni per limitare il ritardo:

- Rame
- Dielettrici *low-k*

